

Lead-free Green DDTD (XXXX) C

NPN PRE-BIASED 500mA SURFACE MOUNT TRANSISTOR

Features

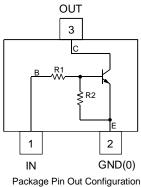
- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTB)
- Built-In Biasing Resistors, R1, R2
- Lead, Halogen and Antimony Free, RoHS Compliant
- "Green" Device (Notes 2 and 3)

Part Number	R1 (NOM)	R2 (NOM)	Marking
DDTD113EC	1K	1K	N60
DDTD123EC	2.2K	2.2K	N61
DDTD143EC	4.7K	4.7K	N62
DDTD114EC	10K	10K	N63
DDTD122JC	0.22K	4.7K	N64
DDTD113ZC	1K	10K	N65
DDTD123YC	2.2K	10K	N66
DDTD133HC	3.3K	10K	N67
DDTD123TC	2.2K	OPEN	N69
DDTD143TC	4.7K	OPEN	N70
DDTD114TC	10K	OPEN	N71
DDTD114GC	0	10K	N72



Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound, Note 3. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating) Solderable per MIL-STD-202, Method 208
- Marking Information: See Table and Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



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Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteris	stic	Symbol	Value	Unit V	
Supply Voltage, (3) to (2)		V _{CC}	50		
Input Voltage, (1) to (2)	DDTD113EC DDTD123EC DDTD143EC DDTD144EC DDTD114EC DDTD122JC DDTD113ZC DDTD123YC DDTD133HC	V _{IN}	-10 to +10 -10 to +12 -10 to +30 -10 to +40 -5 to +5 -5 to +10 -5 to +12 -6 to +20	V	
input Voltage, (2) to (1)	DDTD123TC DDTD143TC DDTD114TC DDTD114TC DDTD114GC	V _{EBO(MAX)}	5	V	
Output Current	All	lc	500	mA	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation	PD	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 1. Mounted on FR4 PC Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead. Halogen and Antimony Free.

 Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.



Electrical Characteristics - R1, R2 Types @T_A = 25°C unless otherwise specified

Characteristic	Characteristic			Тур	Max	Unit	Test Condition
Input Voltage	DDTD113EC DDTD123EC DDTD143EC DDTD144EC DDTD114EC DDTD122JC DDTD113ZC DDTD123YC DDTD133HC	Vi(off)	0.5 0.5 0.5 0.5 0.3 0.3 0.3			V	V _{CC} = 5V, I _O = 100μA
input voltage	DDTD113EC DDTD123EC DDTD143EC DDTD144EC DDTD122JC DDTD122JC DDTD123YC DDTD133HC	V _{I(ON)}			3.0 3.0 3.0 3.0 2.0 2.0 2.0	V	$\begin{array}{l} V_{O}=0.3V,\ I_{O}=20mA\\ V_{O}=0.3V,\ I_{O}=20mA\\ V_{O}=0.3V,\ I_{O}=20mA\\ V_{O}=0.3V,\ I_{O}=10mA\\ V_{O}=0.3V,\ I_{O}=30mA\\ V_{O}=0.3V,\ I_{O}=20mA\\ V_{O}=0.3V,\ I_{O}=20mA\\ V_{O}=0.3V,\ I_{O}=20mA\\ \end{array}$
Output Voltage		V _{O(ON)}	_		0.3V	V	I _O /I _I = -50mA/-2.5mA
Input Current	DDTD113EC DDTD123EC DDTD143EC DDTD144EC DDTD114EC DDTD122JC DDTD113ZC DDTD123YC DDTD133HC	I	_		7.2 3.8 1.8 0.88 28 7.2 3.6 2.4	mA	V ₁ = 5V
Output Current		I _{O(OFF)}			0.5	μA	$V_{CC} = 50V, V_1 = 0V$
DC Current Gain	DDTD113EC DDTD123EC DDTD143EC DDTD144EC DDTD114EC DDTD122JC DDTD113ZC DDTD123YC DDTD133HC	Gı	33 39 47 56 47 56 56 56				V _O = 5V, I _O = 50mA
Input Resistor Tolerance	ΔR_1	-30	—	+30	%	_	
Resistance Ratio Tolerance	$\Delta(R_2/R_1)$	-20	_	+20	%	_	
Gain-Bandwidth Product*		fT		200	_	MHz	V _{CE} = 10V, I _E = 5mA, f = 100MHz

Electrical Characteristics - R1 Only, R2 Only Types @T_A = 25°C unless otherwise specified

Characteristic		Cumhal	Min	T. m	Max	Unit	Test Condition
	Symbol		Тур	wax			
Collector-Base Breakdown Voltage		BV _{CBO}	50	_		V	I _C = 50μA
Collector-Emitter Breakdown Voltage	l	BV _{CEO}	40	_		V	I _C = 1mA
Emitter-Base Breakdown Voltage DDTD123TC DDTD143TC DDTD144TC DDTD114TC DDTD114GC		BV _{EBO}	5		_	V	$I_{E} = 50\mu A$ $I_{E} = 50\mu A$ $I_{E} = 50\mu A$ $I_{E} = 720\mu A$
Collector Cutoff Current	I _{CBO}			0.5	μA	$V_{CB} = 50V$	
Emitter Cutoff Current DDTD123TC DDTD143TC DDTD114TC DDTD114CC		I _{EBO}	 300	_	0.5 0.5 0.5 580	μΑ	V _{EB} = 4V
Collector-Emitter Saturation Voltage		V _{CE(SAT)}			0.3	V	$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 2.5 {\rm mA}$
DC Current Transfer Ratio DC Current Transfer Ratio DDTD143TC DDTD114TC DDTD114CC		h _{FE}	100 100 100 56	250 250 250 —	600 600 600	_	I _C = 50mA, V _{CE} = 5V
Bias Resistor Tolerance	ΔR_1 or ΔR_2	-30	_	+30	%	_	
Gain-Bandwidth Product*	f⊤		200		MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz	

* Transistor - For Reference Only



Ordering Information (Note 4)

Part Number	Case	Packaging		
DDTD113EC-7-F	SOT-23	3000/Tape & Reel		
DDTD123EC-7-F	SOT-23	3000/Tape & Reel		
DDTD143EC-7-F	SOT-23	3000/Tape & Reel		
DDTD114EC-7-F	SOT-23	3000/Tape & Reel		
DDTD122JC-7-F	SOT-23	3000/Tape & Reel		
DDTD113ZC-7-F	SOT-23	3000/Tape & Reel		
DDTD123YC-7-F	SOT-23	3000/Tape & Reel		
DDTD133HC-7-F	SOT-23	3000/Tape & Reel		
DDTD123TC-7-F	SOT-23	3000/Tape & Reel		
DDTD143TC-7-F	SOT-23	3000/Tape & Reel		
DDTD114TC-7-F	SOT-23	3000/Tape & Reel		
DDTD114GC-7-F	SOT-23	3000/Tape & Reel		

Notes: 4. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

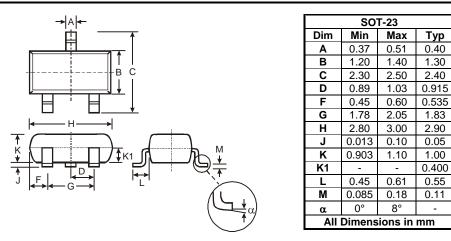
Marking Information



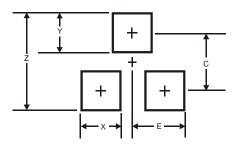
Nxx = Product Type Marking Code (See Page 1) YM = Date Code Marking Y = Year (ex: T = 2002) M = Month (ex: 9 = September)

Date Code Key				_							_			
Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	Ν	Р	R	S	Т	U	V	W	Х	Y	Z	А	В	С
Month	Jan	Feb	M	ar	Apr	Мау	Jun	Jul	Aug	Se	р	Oct	Nov	Dec
Code	1	2	3	3	4	5	6	7	8	9		0	Ν	D

Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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